NSB1706DMW5T1G, NSVB1706DMW5T1G

Dual Bias Resistor Transistor

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the NSB1706DMW5T1G, two BRT devices are housed in the SC–88A package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted, common for } Q_1 \text{ and } Q_2)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	I _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	187 (Note 1) 256 (Note 2) 1.5 (Note 1) 2.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	670 (Note 1) 490 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	250 (Note 1) 385 (Note 2) 2.0 (Note 1) 3.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	493 (Note 1) 325 (Note 2)	°C/W
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	188 (Note 1) 208 (Note 2)	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

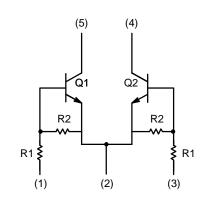
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 inch Pad.



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MARKING DIAGRAM



U6 = Device Marking

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSB1706DMW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel
NSVB1706DMW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSB1706DMW5T1G, NSVB1706DMW5T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, common for Q_1 and Q_2)

Characteristic	Symbo	l Min	Тур	Max	Unit
OFF CHARACTERISTICS	·				•
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_{E} = 0)$	Ісво	-	_	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	-	_	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_{C} = 0)$	I _{EBO}	-	_	0.18	mAdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _{(BR)CB}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 3) (I _C = 2.0 mA, I _B = 0)	V _{(BR)CE}	50	-	-	Vdc
ON CHARACTERISTICS (Note 3)		•	•	•	
DC Current Gain $(V_{CE} = 10 \text{ V}, I_{C} = 5.0 \text{ mA})$	h _{FE}	80	200	-	
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 1 mA)	V _{CE(sat)}	-	-	0.25	Vdc
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μ A)	V _{i(off)}	-	0.6	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3 \text{ V}, I_{C} = 5 \text{ mA}$)	V _{i(on)}	1.3	0.9	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	-	_	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R1/R2	0.055	0.1	0.185	

 ${\it NOTE:}\ New\ resistor\ combinations.\ Updated\ curves\ to\ follow\ in\ subsequent\ data\ sheets.$

^{3.} Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%.

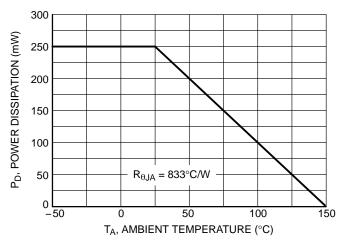


Figure 1. Derating Curve





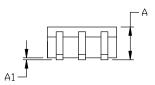
SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

DATE 11 APR 2023

NOTES:

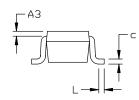
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSOLETE, NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,
 OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

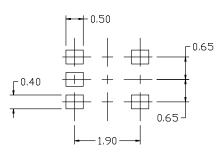
DIM	MILLIMETERS			
ויודע	MIN.	N□M.	MAX.	
А	0.80	0.95	1.10	
A1			0.10	
A3	0,20 REF			
b	0.10	0.20	0.30	
С	0.10		0.25	
D	1.80	2.00	2,20	
Е	2.00	2.10	2.20	
E1	1.15	1.25	1.35	
е	0.65 BSC			
L	0.10	0.15	0.30	



5X b

◆ 0.2 M B M





RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

DR
DR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1 STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:

98ASB42984B

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DESCRIPTION:

5. COLLECTOR 2/BASE 1

SC-88A (SC-70-5/SOT-353)

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